

*Sub ES*

45. The device of claim 6 wherein said channel formation region is crystallized by laser irradiation through an insulating film.

46. The device of claim 7 wherein said channel formation region is crystallized by laser irradiation through [an insulating film].

47. The device of claim 8 wherein said channel formation region is crystallized by laser irradiation through an insulating film.

48. The device of claim 19 wherein said channel formation region is crystallized by laser irradiation through an insulating film.

*1*  
*contd*

49. The device of claim 20 wherein said channel formation region is crystallized by laser irradiation through an insulating film.

50. The device of claim 21 wherein said channel formation region is crystallized by laser irradiation through an insulating film.

51. The device of claim 22 wherein said channel formation region is crystallized by laser irradiation through an insulating film.

52. The device of claim 23 wherein said channel formation region is crystallized by laser irradiation through an insulating film.

53. The device of claim 24 wherein said channel formation region is crystallized by laser irradiation through an insulating film.

*Fig. 12E*

54. An active matrix type liquid crystal display comprising:  
a substrate having a front surface and a rear surface;  
an aluminum nitride insulating film containing therein at least one of carbon and oxygen provided under said rear surface of the substrate; and  
a transistor provided over said front surface of the substrate, said transistor having at least a channel formation region comprising crystalline silicon, a gate insulating film adjacent to said channel formation region, and a gate electrode adjacent to said channel formation region with said gate insulating film interposed therebetween;

Sub E57  
an interlayer insulating film having a leveled upper surface over [said thin  
film transistor]; and  
a pixel electrode over said interlayer insulating film.

55. The device of claim 54 wherein said channel formation region is  
crystallized by laser irradiation through an insulating film.

56. The device of claim 54 wherein said substrate is a glass substrate.

57. An active matrix type liquid crystal display comprising:  
a substrate having a front surface and a rear surface;  
an aluminum nitride insulating film containing therein at least one of  
carbon and oxygen provided over said front surface of the substrate;  
a transistor provided over said aluminum nitride insulating film, said  
transistor having at least a channel formation region comprising crystalline silicon, a gate  
insulating film adjacent to said channel formation region, and a gate electrode adjacent to  
said channel formation region with said gate insulating film interposed therebetween;  
an interlayer insulating film having a leveled upper surface over [said thin  
film transistor]; and  
a pixel electrode over said interlayer insulating film.

12E  
9  
10

58. The device of claim 57 wherein said channel formation region is  
crystallized by laser irradiation through an insulating film.

59. The device of claim 57 wherein said substrate is a glass substrate.--

Add E7  
BEST AVAILABLE COPY